

Abstract of the Disclosure

A method of forming an encapsulating spacer prior to gate stack reoxidation is provided which prevents the formation of undesirable metal oxides during reoxidation. A material such as a thin silicon nitride or amorphous silicon is selectively deposited by 5 limiting deposition time to a period less than incubation time. As a result spacers are formed without having to perform an additional etch act.

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